



AO5804E

Dual N-Channel Enhancement Mode Field Effect Transistor

General Description

The AO5804E/L uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications. AO5804E and AO5804EL are electrically identical.

- RoHS Compliant
- AO5804EL is Halogen Free

Features

- $V_{DS} (V) = 20V$
- $I_D = 0.5 A (V_{GS} = 4.5V)$
- $R_{DS(ON)} < 0.55\Omega (V_{GS} = 4.5V)$
- $R_{DS(ON)} < 0.68\Omega (V_{GS} = 2.5V)$
- $R_{DS(ON)} < 0.80\Omega (V_{GS} = 1.8V)$

ESD PROTECTED!



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	10 Sec	Steady State	Units
Drain-Source Voltage	V_{DS}	20		V
Gate-Source Voltage	V_{GS}	± 8		V
Continuous Drain Current ^{A, F}	I_D	$T_A=25^\circ C$	0.5	A
		$T_A=70^\circ C$	0.5	
Pulsed Drain Current ^B	I_{DM}	3		
Power Dissipation ^A	P_D	$T_A=25^\circ C$	0.38	W
		$T_A=70^\circ C$	0.24	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150		$^\circ C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	275	330	$^\circ C/W$
Maximum Junction-to-Ambient ^A		Steady-State	360	450
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	300	350	$^\circ C/W$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$	20			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=20\text{V}, V_{GS}=0\text{V}$			1	μA
		$T_J=55^{\circ}\text{C}$			5	
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}=\pm 4.5\text{V}$			± 1	μA
		$V_{DS}=0\text{V}, V_{GS}=\pm 8\text{V}$			± 100	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	0.45	0.6	1	V
$I_{D(ON)}$	On state drain current	$V_{GS}=4.5\text{V}, V_{DS}=5\text{V}$	3			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=4.5\text{V}, I_D=0.5\text{A}$		0.4	0.55	Ω
		$T_J=125^{\circ}\text{C}$		0.6	0.85	
		$V_{GS}=2.5\text{V}, I_D=0.5\text{A}$		0.48	0.68	Ω
		$V_{GS}=1.8\text{V}, I_D=0.3\text{A}$		0.6	0.8	Ω
g_{FS}	Forward Transconductance	$V_{DS}=5\text{V}, I_D=0.5\text{A}$		1.5		S
V_{SD}	Diode Forward Voltage	$I_S=0.1\text{A}, V_{GS}=0\text{V}$		0.65	1	V
I_S	Maximum Body-Diode Continuous Current				0.4	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance			35	45	pF
C_{oss}	Output Capacitance	$V_{GS}=0\text{V}, V_{DS}=10\text{V}, f=1\text{MHz}$		8		pF
C_{rss}	Reverse Transfer Capacitance			6		pF
SWITCHING PARAMETERS						
Q_g	Total Gate Charge			0.63	1	nC
Q_{gs}	Gate Source Charge	$V_{GS}=4.5\text{V}, V_{DS}=10\text{V}, I_D=0.5\text{A}$		0.08		nC
Q_{gd}	Gate Drain Charge			0.16		nC
$t_{D(on)}$	Turn-On Delay Time			4.5		ns
t_r	Turn-On Rise Time	$V_{GS}=5\text{V}, V_{DS}=10\text{V}, R_L=50\Omega,$ $R_{GEN}=3\Omega$		3.3		ns
$t_{D(off)}$	Turn-Off Delay Time			78		ns
t_f	Turn-Off Fall Time			32		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=0.5\text{A}, dI/dt=100\text{A}/\mu\text{s}$		8	10	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=0.5\text{A}, dI/dt=100\text{A}/\mu\text{s}$		2		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The value in any given application depends on the user's specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6,12,14 are obtained using $<300 \mu\text{s}$ pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The SOA curve provides a single pulse rating.

F: The maximum current rating is limited by bond-wires

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

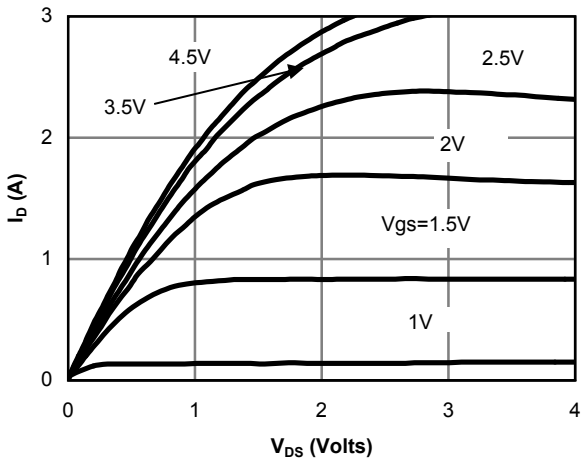


Figure 1: On-Region Characteristics

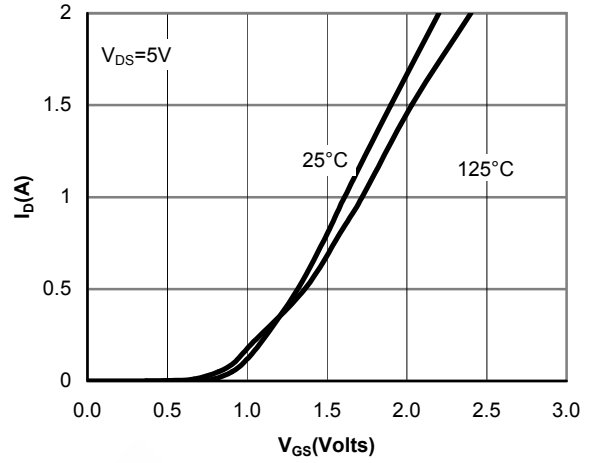


Figure 2: Transfer Characteristics

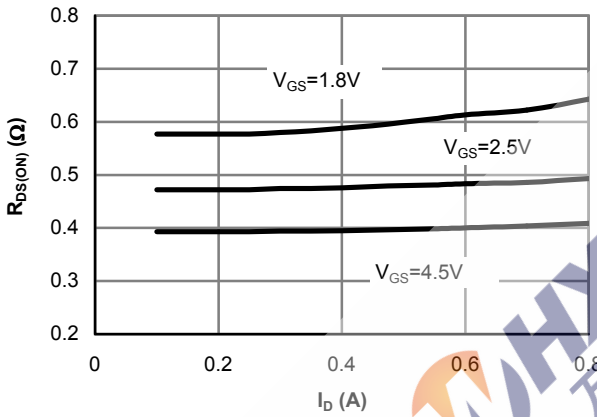


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

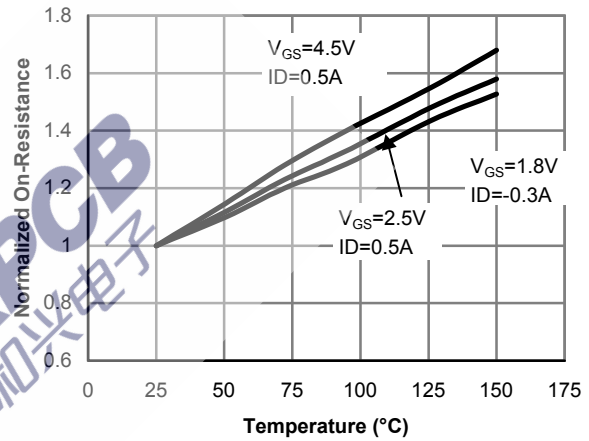


Figure 4: On-Resistance vs. Junction Temperature

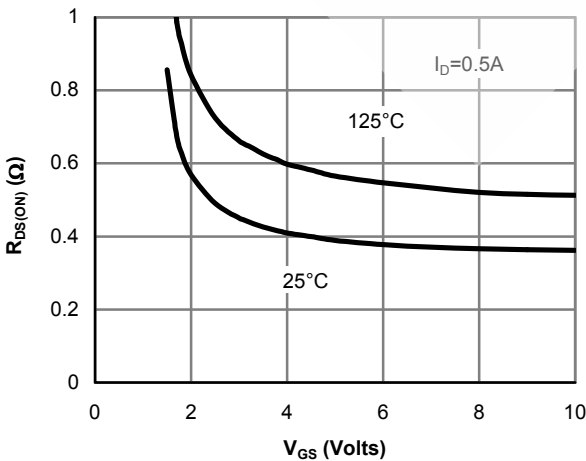


Figure 5: On-Resistance vs. Gate-Source Voltage

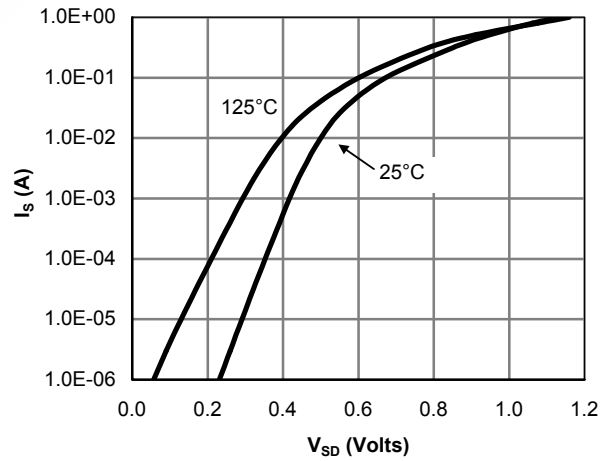


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

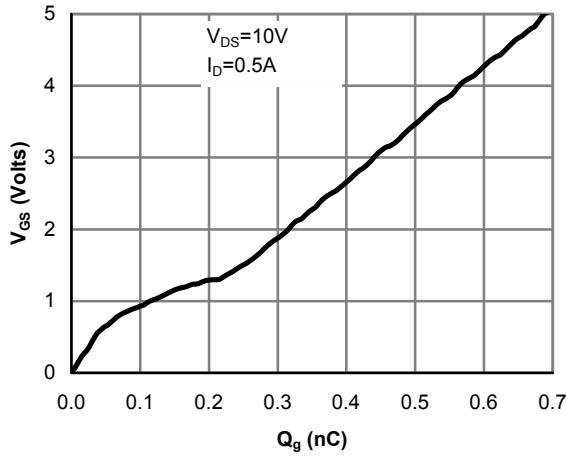


Figure 7: Gate-Charge Characteristics

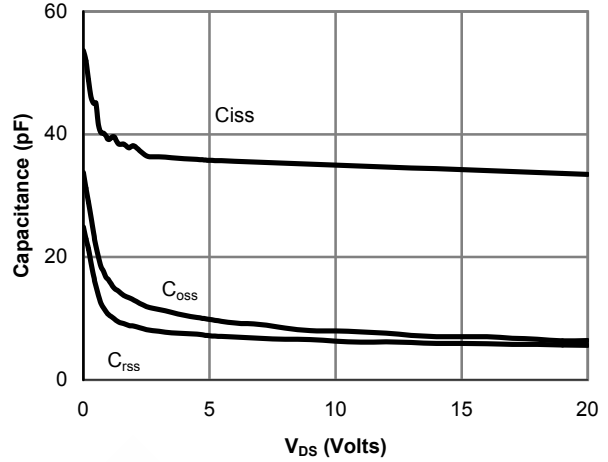


Figure 8: Capacitance Characteristics

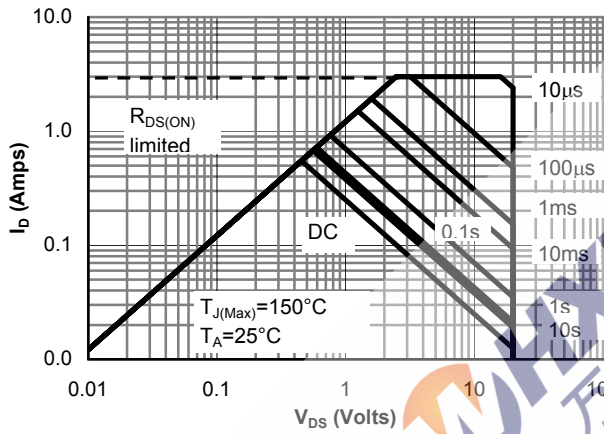


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

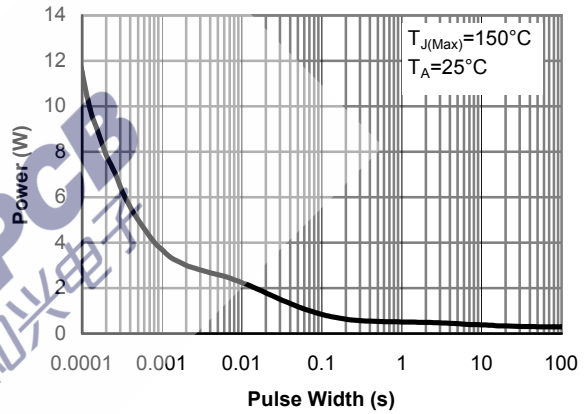


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

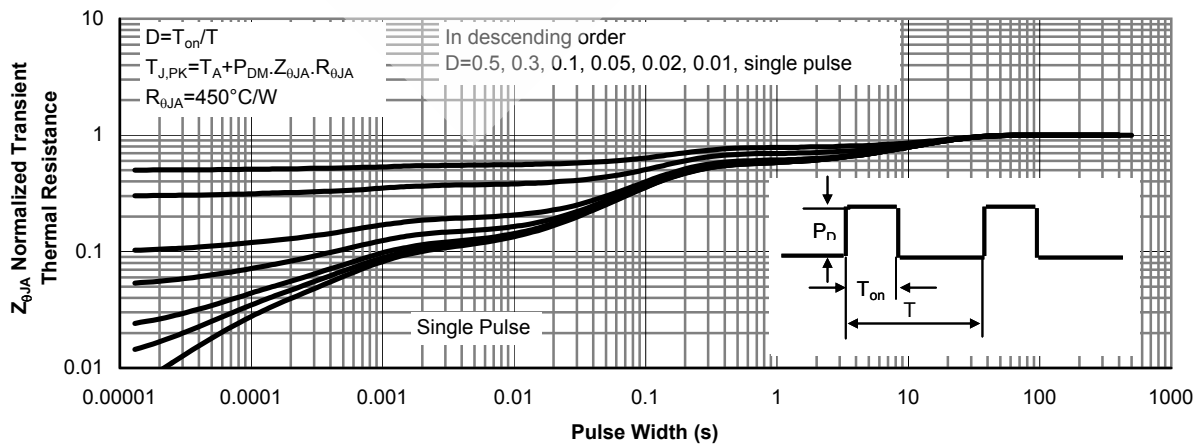
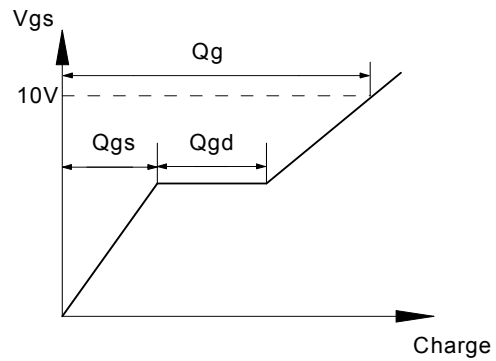
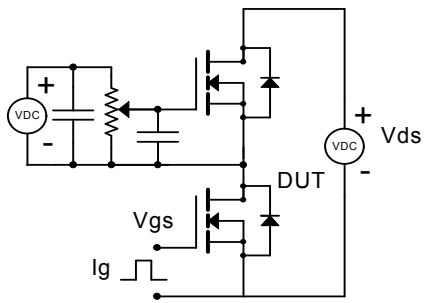
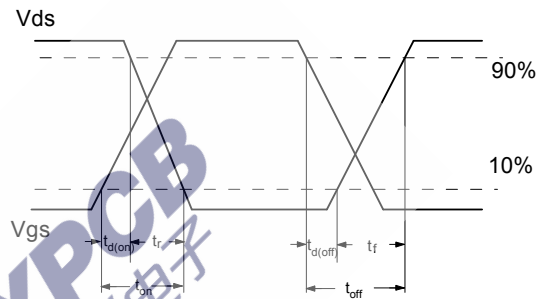
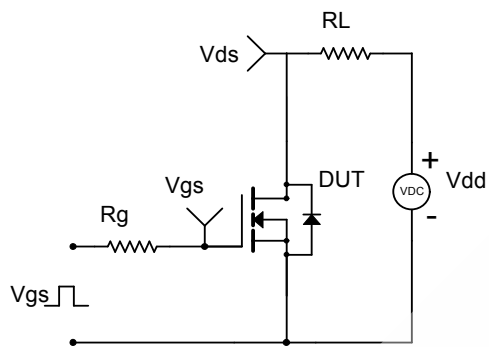


Figure 11: Normalized Maximum Transient Thermal Impedance

Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

